ON Semiconductor®



Plastic High Power Silicon Transistor

... designed for use in high power audio amplifiers utilizing complementary or quasi complementary circuits.

• DC Current Gain —

$h_{FE} = 30 \text{ (Min)} @ I_C = 2.0$	Adc				
MAXIMUM RATINGS					
Rating	Symbol	Value	Unit		
Collector-Emitter Voltage	VCEO	80	Vdc		
Collector-Base Voltage	V _{CBO}	80	Vdc		
Emitter-Base Voltage	V _{EBO}	5.0	Vdc		
Collector Current	IC	10	Adc		
Base Current	IΒ	6.0	Adc		
Total Device Dissipation T _C = 25°C Derate above 25°C	PD	90 720	Watts mW/°C		
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C		

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θJC	1.39	°C/W

NPN **BD809 PNP BD810**

10 AMPERE **POWER TRANSISTORS PNP SILICON** 60, 80 VOLTS **90 WATTS**





ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Collector–Emitter Sustaining Voltage* (I _C = 0.1 Adc, I _B = 0)	BVCEO	80		Vdc
Collector Cutoff Current (VCB = 80 Vdc, IE = 0)	ICBO	_	1.0	mAdc
Emitter Cutoff Current (VBE = 5.0 Vdc, I _C = 0)	I _{EBO}	_	2.0	mAdc
DC Current Gain (I _C = 2.0 A, V _{CE} = 2.0 V) (I _C = 4.0 A, V _{CE} = 2.0 V)	hFE	30 15		
Collector–Emitter Saturation Voltage* (IC = 3.0 Adc, I _B = 0.3 Adc)	VCE(sat)	_	1.1	Vdc
Base–Emitter On Voltage* (IC = 4.0 Adc, VCE = 2.0 Vdc)	V _{BE(on)}	_	1.6	Vdc
Current–Gain Bandwidth Product (I _C = 1.0 Adc, V _{CE} = 10 Vdc, f = 1.0 MHz)	fT	1.5	_	MHz

^{*}Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

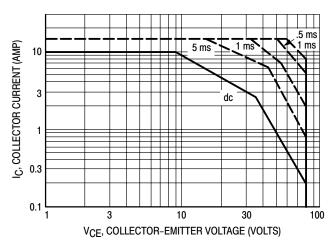


Figure 1. Active Region DC Safe Operating Area (see Note 1)

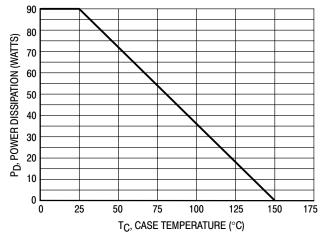


Figure 2. Power-Temperature Derating Curve

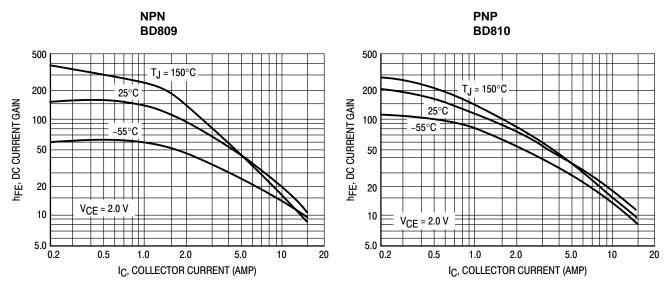


Figure 3. DC Current Gain

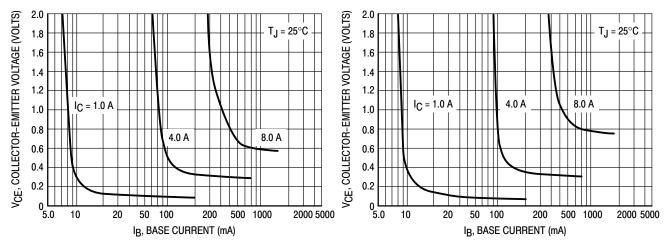


Figure 4. Collector Saturation Region

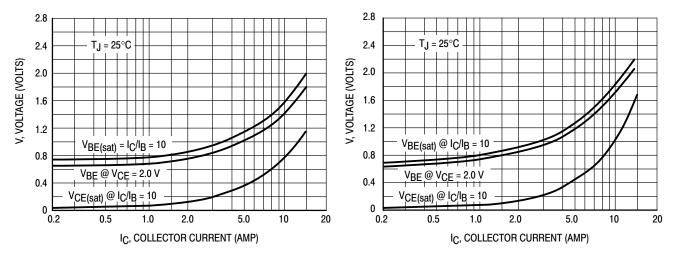


Figure 5. "On" Voltages

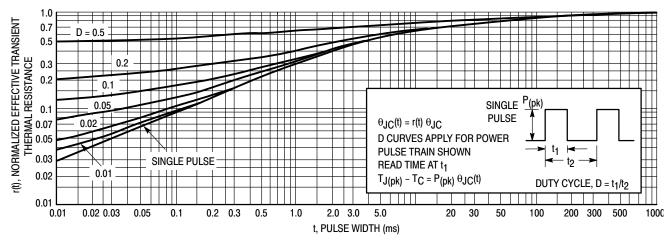


Figure 6. Thermal Response

Note 1:

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_{\hbox{\scriptsize C}}-V_{\hbox{\scriptsize CE}}$ limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

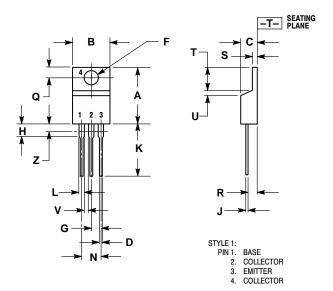
The data of Figure 1 is based on $T_{J(pk)} = 150^{\circ}C$; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}C$. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

Notes

Notes

PACKAGE DIMENSIONS

TO-220 CASE 221A-09 **ISSUE AA**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INC	HES	MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
Н	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

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